Amendments to the Claims

Claims 1-11 (canceled).

12. (new) A method of making a white light source, comprising: encapsulating a light-emitting diode in an epoxy resin having a phosphor dispersed therein, the light emitting diode having an emission from 420 to 490 nm, and the phosphor having a garnet structure as represented by $A_3B_5O_{12}$:Ce wherein A is terbium or terbium together with at least one of the elements Y, Gd, La, and/or Lu and B is at least one of the elements Al and Ga, the phosphor converting at least a part of the emission from the light-emitting diode into a longer-wave radiation.

13. (new) The method of claim 12 wherein A is solely or predominately terbium.

14. (new) The method of claim 12 wherein the light-emitting diode has an emission from 430 to 470 nm.

15. (new) The method of claim 13 wherein the light-emitting diode has an emission from 430 to 470 nm.

16. (new) The method of claim 12 wherein B additionally contains In.

17. (new) The method of claim 12 wherein the light-emitting diode is based on Ga(In)N.

18. (new) A method of making a white light source, comprising: encapsulating a light-emitting diode in an epoxy resin having a phosphor dispersed therein, the light emitting diode having an emission from 420 to 490 nm, the phosphor converting at least a portion of the emission from the light-emitting diode into a longer-wave radiation and having a garnet structure represented by

$(Tb_{1-x-y}RE_xCe_y)_3(Al,Ga)_5O_{12}$, where
RE is Y, Gd, La and/or Lu;
$0 \leq x \leq 0.5-y$; and
$0 < y < 0.1$.

19. (new) The method of claim 18 wherein x is in the range $0.25 \leq x \leq 0.5-y$.

20. (new) The method of claim 18 wherein y is in the range $0.02 < y < 0.06$.

21. (new) The method of claim 18 wherein x is in the range $0.25 \leq x \leq 0.5\text{-}y$ and y is in the range $0.02 < y < 0.06$.

22. (new) The method of claim 18 wherein the light source has a color temperature of below 5000 K.

23. (new) The method of claim 18 wherein the light source has a color temperature of 4500 K.

24. (new) The method of claim 12 wherein the phosphor contains from 0.03 to less than 3 moles of terbium per mole of phosphor.

25. (new) The method of claim 18 wherein the light-emitting diode is based on Ga(In)N.

26. (new) A method of making a white light source, comprising: encapsulating a light-emitting diode in an epoxy resin having a phosphor dispersed therein, the light emitting diode having an emission from 420 to 490 nm, the phosphor converting at least a portion of the emission from the light-emitting diode into a longer-wave radiation, the phosphor having a garnet structure represented by

$(Tb_xRE_{1-x-y}Ce_y)_3(Al,Ga)_5O_{12}$, where
RE is Y, Gd, La and/or Lu;
$0.01 \leq x \leq 0.02$; and
$0 < y < 0.1$.

27. (new) The method of claim 26 wherein x is 0.01.

28. (new) The method of claim 26 wherein y is in the range $0.01 \leq y \leq 0.05$.

29. (new) The method of claim 27 wherein y is in the range $0.01 \leq y \leq 0.05$.

30. (new) The method of claim 27 wherein the phosphor has a garnet structure represented by $(Y_{0.50}, Gd_{0.45}Tb_{0.01}Ce_{0.04})_3Al_5O_{12}$.

31. (new) The method of claim 26 wherein the light-emitting diode is based on Ga(In)N.